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(54) Title: METHOD FOR MANUFACTURING A SEMICONDUCTOR ON INSULATOR TYPE STRUCTURE BY LAYER TRANSFER

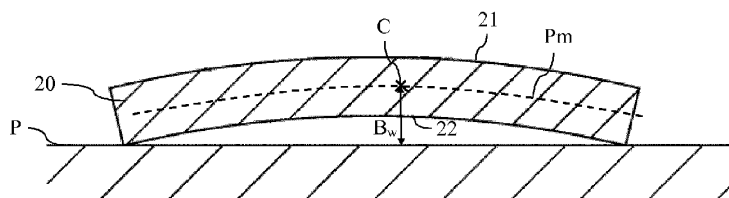


FIGURE 3B

(57) Abstract: The invention relates to a method for manufacturing a semiconductor on insulator type structure by transfer of a layer from a donor substrate onto a receiver substrate, comprising the following steps: a) the supply of the donor substrate and the receiver substrate, b) the formation in the donor substrate of an embrittlement zone delimiting the layer to transfer, c) the bonding of the donor substrate on the receiver substrate, the surface of the donor substrate opposite to the embrittlement zone with respect to the layer to transfer being at the bonding interface, d) the detachment of the donor substrate along the embrittlement zone enabling the transfer of the layer to transfer onto the receiver substrate, the transfer method being characterised in that it comprises, before the bonding step, a step of controlled modification of the curvature of the donor substrate and/or the receiver substrate so as to move the substrates away from each other at least in one region of their periphery, the face or the two faces intended to form the bonding interface of the donor substrate and/or the receiver substrate being deformed so as to have a curvature amplitude (Bw) greater than or equal to 136 μm .

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